Abstract

Method for slicing a multiplicity of wafers from a crystal composed of semiconductor material

A method for slicing a multiplicity of wafers from a crystal composed of semiconductor material and having a longitudinal axis and a cross section, wherein the crystal fixed on a table is guided by a relative movement between the table and the wire gang of a wire saw, said relative movement being directed perpendicularly to the longitudinal axis of the crystal, through the wire gang formed with sawing wire in such a way that the entry sawing effected by the sawing wire takes place in the vicinity of a pulling edge of the crystal or the exit sawing effected by the sawing wire takes place in the vicinity of a pulling edge of the crystal.

Fig. 1